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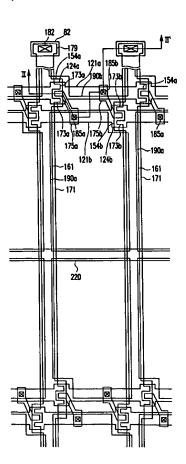
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### (54) Title: THIN FILM TRANSISTOR ARRAY PANEL



(57) Abstract: A thin film transistor ("TFT") array panel is provided, which includes: first and second gate lines transmitting gate signals to adjacent pixel rows and disposed adjacent to each other; a data line insulated from the first and the second gate lines and the data line; a first thin film transistor connected to the first gate line and the data line and including a first drain electrode overlapping the second gate line; a second TFT connected to the second gate line and the data line, disposed opposite the first TFT with respect to the data line, and including a second drain electrode overlapping the first gate line; a first pixel electrode connected to the first drain electrode and overlapping the second gate line; and a second pixel electrode connected to the second electrode and overlapping the first gate line.

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